

Search history

STN

(HCAPLUS, INSPEC, JAPIC, ZEPATENT)

3/14/05

=> d 18 1-17 abs,bib

L8 ANSWER 1 OF 17 HCAPLUS COPYRIGHT 2005 ACS on STN
AB A **photonic crystal** manufacturing method exposes ≥ 2 Ag halide particle layers that contain Ag halide particles which have different spectral sensitivity characteristics for each of the Ag halide particle layers to light having **wavelengths** corresponding to the resp. different spectral sensitivity characteristics, and then develops the exposed Ag halide particle layers to form therein a periodic structure with an aggregate of developed Ag. **Photonic crystals** can be manufactured with relative ease in a relatively short period of time. This method assures continued high accuracy.

AN 2004:251809 HCAPLUS

DN 140:278343

TI Method of manufacturing **photonic crystal**

IN Miyazaki, Keiichi

PA Fuji Photo Film Co., Ltd., Japan

SO U.S. Pat. Appl. Publ., 7 pp.

CODEN: USXXCO

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004055528	A1	20040325	US 2003-667361	20030923
	JP 2004117479	A2	20040415	JP 2002-276867	20020924
PRAI	JP 2002-276867	A	20020924		

L8 ANSWER 2 OF 17 HCAPLUS COPYRIGHT 2005 ACS on STN

AB A single-beam holog. method for one-step fabrication of three-dimensional (3D) metallocdielec. **photonic crystals** is demonstrated using a 632.8 nm He-Ne laser. A top-cut triangular prism is used to split an incident plane wave into four beams and then to combine them to form a 3D interference pattern. A **silver halide** holog. plate is used to record the interference pattern and then a 3D structure with embedded Ag particles is created. A strongly damping band around 1400 nm is observed in the transmission spectrum of this 3D structure.

AN 2003:733735 HCAPLUS

DN 140:311525

TI Holography for one-step fabrication of three-dimensional metallocdielectric **photonic crystals** with a single continuous *Applicant's Invention* wavelength laser beam

AU Wang, Guo Ping; Tan, Chunlei; Yi, Xiangxiang; Shan, Hong

CS Dep. of Phys., and Sch. of Computer Sci., Wuhan Univ., Wuhan, 430072, Peop. Rep. China

SO Journal of Modern Optics (2003), 50(14), 2155-2161

CODEN: JMOPEW; ISSN: 0950-0340

PB Taylor & Francis Ltd.

DT Journal

LA English

RE.CNT 20 THERE ARE 20 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L8 ANSWER 3 OF 17 INSPEC (C) 2005 IEE on STN

AN 2004:7903470 INSPEC DN A2004-09-4240-015; B2004-04-4350-079

AB A single-beam holographic method for one-step fabrication of three-dimensional (3D) metallocdielectric **photonic crystals** is demonstrated using a 632.8 nm He-Ne laser. A top-cut triangular prism is used to split an incident plane wave into four beams and then to combine them to form a 3D interference pattern. A **silver halide** holographic plate is used to record the interference pattern and then a 3D structure with embedded Ag particles is created. A strongly damping band around 1400 nm is observed in the

transmission spectrum of this 3D structure.

DN A2004-09-4240-015; B2004-04-4350-079

TI Holography for one-step fabrication of three-dimensional metallocodielectric photonic crystals with a single continuous wavelength laser beam.

AU Guo Ping Wang; Chunlei Tan; Yongxiang Yi; Hong Shan (Dept. of Phys., Wuhan Univ., China)

SO Journal of Modern Optics (20 Sept. 2003) vol.50, no.14, p.2155-61. 20 refs.
Published by: Taylor & Francis
CODEN: JMOPEW ISSN: 0950-0340
SICI: 0950-0340(20030920)50:14L.2155:HSFT;1-#

DT Journal
TC Experimental
CY United Kingdom
LA English

L8 ANSWER 4 OF 17 JAPIO (C) 2005 JPO on STN

AN 2004-117479 JAPIO

AB PROBLEM TO BE SOLVED: To provide a manufacturing method for photonic crystal in which the photonic crystal can be manufactured relatively easily in a relatively short time and further a manufacturing method for photonic crystal which can maintain high precision.
SOLUTION: The present invention is characterized in that two or more silver halide layers containing silver halide particles with mutually different spectral sensitivity characteristics are exposed to lights having wavelengths corresponding to the different spectral sensitivity characteristics and developed to form periodic structures of aggregates of developed silver in the silver halide particle layers.

COPYRIGHT: (C) 2004 JPO

AN 2004-117479 JAPIO

TI METHOD FOR MANUFACTURING PHOTONIC CRYSTAL

IN MIYAZAKI KEIICHI

PA FUJI PHOTO FILM CO LTD

PI JP 2004117479 A 20040415 Heisei

AI JP 2002-276867 (JP2002276867 Heisei) 20020924

PRAI JP 2002-276867 20020924

SO PATENT ABSTRACTS OF JAPAN (CD-ROM), Unexamined Applications, Vol. 2004

L8 ANSWER 5 OF 17 USPATFULL on STN

AB A novel anisotropic spectral scattering film is disclosed. The scattered light intensity $F_x(\lambda, \theta)$ at azimuthal angle θ and incident wavelength λ in an arbitrary scattering plane with respect to a surface of the film, and the scattered light intensity $F_y(\lambda, \theta)$ at azimuthal angle θ and incident wavelength λ in a scattering plane orthogonal to said scattering plane satisfy the following equations (1) and (2):

$$F_x(\lambda, \theta)/F_x(545, \theta) \geq 1.2 \quad (1)$$
$$\{F_x(\lambda, \theta)/F_x(545, \theta) - F_y(\lambda, \theta)/F_y(545, \theta)\} \geq 0.1 \quad (2)$$

provided that λ is 435 or 610 nm and θ is an arbitrary angle selected from 30-70°.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2005:2856 USPATFULL

TI Anisotropic spectral scattering films, polarizers and liquid crystal displays

IN Amimori, Ichiro, Minami-ashigara-shi, JAPAN

PA Fujiwara, Isao, Minami-ashigara-shi, JAPAN
Fuji Photo Film Co., Ltd., Minami-ashigara-shi, JAPAN (non-U.S.
corporation)

PI US 2005001957 A1 20050106

AI US 2004-845264 A1 20040514 (10)

PRAI JP 2003-138772 20030516

JP 2003-138773 20030516

DT Utility

FS APPLICATION

LREP BURNS DOANE SWECKER & MATHIS L L P, POST OFFICE BOX 1404, ALEXANDRIA,
VA, 22313-1404

CLMN Number of Claims: 13

ECL Exemplary Claim: 1

DRWN 8 Drawing Page(s)

LN.CNT 1573

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 6 OF 17 USPATFULL on STN

AB Wafer-level electronic packages having waveguides and methods of
fabricating chip-level electronic packages having waveguides are
disclosed. A representative chip-level electronic package includes at
least one waveguide having a waveguide core. In addition, another
representative chip-level electronic package includes a waveguide having
an air-gap cladding layer around a portion of the waveguide core. A
representative method for fabricating a chip-level electronic package
includes: providing a substrate having a passivation layer disposed on
the substrate; disposing a waveguide core on a portion of the
passivation layer; disposing a first sacrificial layer onto at least one
portion of the passivation layer and the waveguide core; disposing an
overcoat layer onto the passivation layer and the first sacrificial
layer; and removing the first sacrificial layer to define an air-gap
cladding layer within the overcoat polymer layer and around a portion of
the waveguide core.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2004:333764 USPATFULL

TI Guided-wave optical interconnections embedded within a microelectronic
wafer-level batch package

IN Mule, Tony, Atlanta, GA, UNITED STATES
Patel, Chirag, Jonesboro, GA, UNITED STATES
Meindl, James D., Marietta, GA, UNITED STATES
Gaylord, Thomas K., Atlanta, GA, UNITED STATES
Glytsis, Elias N., Dunwoody, GA, UNITED STATES
Martin, Kevin P., Atlanta, GA, UNITED STATES
Schultz, Stephen M., Spanish Fork, UT, UNITED STATES
Bakir, Muhamnad, Atlanta, GA, UNITED STATES
Reed, Hollie, Smyrna, GA, UNITED STATES
Kohl, Paul, Atlanta, GA, UNITED STATES

PI US 2004264840 A1 20041230

AI US 2004-895685 A1 20040721 (10)

RLI Continuation of Ser. No. US 2002-74420, filed on 11 Feb 2002, GRANTED,
Pat. No. US 6785458

PRAI US 2001-268142P 20010211 (60)

DT Utility

FS APPLICATION

LREP THOMAS, KAYDEN, HORSTEMEYER & RISLEY, LLP, 100 GALLERIA PARKWAY, NW, STE
1750, ATLANTA, GA, 30339-5948

CLMN Number of Claims: 11

ECL Exemplary Claim: CLM-01-30

DRWN 40 Drawing Page(s)

LN.CNT 1528

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 7 OF 17 USPATFULL on STN

AB Continous, conducting metal patterns can be formed from metal nanoparticle containing fils by exposure to radiation. The metal patterns can be one, two, or three dimensional and have high resolution resulting in feature sizes in the order of micron to nanometers

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2004:104811 USPATFULL

TI Method for patterning metal using nanopraticle containing precursors

IN Perry, Joseph W., Tucson, AZ, UNITED STATES

Marder, Seth R., Tucson, AZ, UNITED STATES

Stellacci, Francesco, Tucson, AZ, UNITED STATES

PI US 2004079195 A1 20040429

AI US 2003-450661 A1 20031215 (10)

WO 2001-US47724 20011217

DT Utility

FS APPLICATION

LREP OBLON, SPIVAK, MCCLELLAND, MAIER & NEUSTADT, P.C., 1940 DUKE STREET, ALEXANDRIA, VA, 22314

CLMN Number of Claims: 73

ECL Exemplary Claim: 1

DRWN 24 Drawing Page(s)

LN.CNT 2486

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 8 OF 17 USPATFULL on STN

AB A feedback-enhanced light emitting device is disclosed. A feedback element coupled to an emissive element allows the emissive element to emit collimated light by stimulated emission. Feedback elements that provide this function may include but are not limited to holographic reflectors with refractive index that varies at least in part periodically and continuously.

AN 2004:92555 USPATFULL

TI Feedback enhanced light emitting device

IN Magno, John N., Middletown, NJ, UNITED STATES

Koch, Gene C., Bayville, NJ, UNITED STATES

PA Zeolux Corporation, Sammamish, WA, UNITED STATES (U.S. corporation)

PI US 2004069995 A1 20040415

AI US 2003-434941 A1 20030508 (10)

PRAI US 2002-379141P 20020508 (60)

DT Utility

FS APPLICATION

LREP BAKER & MCKENZIE, 805 THIRD AVENUE, NEW YORK, NY, 10022

CLMN Number of Claims: 127

ECL Exemplary Claim: 1

DRWN 11 Drawing Page(s)

LN.CNT 1748

L8 ANSWER 9 OF 17 USPATFULL on STN

AB A photonic crystal manufacturing method exposes two or more silver halide particle layers that contain silver halide particles which have different spectral sensitivity characteristics for each of the silver halide particle layers to light having wavelengths corresponding to the respective different spectral sensitivity characteristics, and then develops the exposed silver halide particle layers to form therein a periodic structure with an aggregate of developed silver. Photonic crystals can be manufactured with relative ease in a relatively short period of time. This method assures continued high accuracy.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2004:73766 USPATFULL
TI Method of manufacturing photonic crystal
IN Miyazaki, Keiichi, Kanagawa, JAPAN
PA FUJI PHOTO FILM CO., LTD. (now U.S. corporation)
PI US 2004055528 A1 20040325
AI US 2003-667361 A1 20030923 (10)
PRAI JP 2002-276867 20020924
DT Utility
FS APPLICATION
LREP SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W., SUITE 800,
WASHINGTON, DC, 20037
CLMN Number of Claims: 9
ECL Exemplary Claim: 1
DRWN 2 Drawing Page(s)
LN.CNT 359
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 10 OF 17 USPATFULL on STN
AB Optoelectronic probe cards, methods of fabrication, and methods of use, are disclosed. Briefly described, one exemplary embodiment includes an optoelectronic probe card adapted to test an electrical quality and an optical quality of an optoelectronic structure under test having electrical and optical components.

AN 2004:23382 USPATFULL
TI High input/output density optoelectronic probe card for wafer-level test of electrical and optical interconnect components, methods of fabrication, and methods of use
IN Mule, Tony, Atlanta, GA, UNITED STATES
Thacker, Hiren, Decatur, GA, UNITED STATES
Bakir, Muhamnad, Atlanta, GA, UNITED STATES
Meindl, James D., Marietta, GA, UNITED STATES
Gaylord, Thomas K., Atlanta, GA, UNITED STATES
Martin, Kevin P., Atlanta, GA, UNITED STATES
Kohn, Paul, Atlanta, GA, UNITED STATES
PI US 2004017215 A1 20040129
AI US 2003-390873 A1 20030317 (10)
PRAI US 2002-365443P 20020319 (60)
DT Utility
FS APPLICATION
LREP THOMAS, KAYDEN, HORSTEMEYER & RISLEY, LLP, 100 GALLERIA PARKWAY, NW, STE 1750, ATLANTA, GA, 30339-5948
CLMN Number of Claims: 54
ECL Exemplary Claim: 1
DRWN 4 Drawing Page(s)
LN.CNT 1017

L8 ANSWER 11 OF 17 USPATFULL on STN
AB A light control material is provided for displaying color images having microstructures either on its surface or within the material which reflect a selected color and bandwidth of light in accordance with their physical characteristics. In an exemplary embodiment, the microstructures are stepped structures which reflect a particular color and bandwidth of light in accordance with the height of the steps of the stepped structures. In alternative embodiment, the microstructures are ribbed structures or crystal like structures designed to reflect a selected color and bandwidth of light. In addition, methods of fabricating the material are provided.

AN 2003:329968 USPATFULL
TI Light control material for displaying color information, and images
IN Steenblik, Richard A., Alpharetta, GA, UNITED STATES
Hurt, Mark J., Duluth, GA, UNITED STATES

PA Knotts, Michael E., Roswell, GA, UNITED STATES
PI Nanoventions, Inc., Roswell, GA (U.S. corporation)
AI US 2003232179 A1 20031218
PRAI US 2003-351286 A1 20030123 (10)
US 2002-352000P 20020124 (60)
US 2002-351853P 20020124 (60)
DT Utility
FS APPLICATION
LREP Todd Deveau, Thomas, Kayden, Horstemeyer & Risley, LLP, Suite 1750, 100
Galleria Parkway, Atlanta, GA, 30339
CLMN Number of Claims: 32.
ECL Exemplary Claim: 1
DRWN 22 Drawing Page(s)
LN.CNT 1512

L8 ANSWER 12 OF 17 USPATFULL on STN

AB The optical functional element contains aggregates of developed silver grains obtained by developing **silver halide** grains arranged so as to constitute a periodical structure. The element includes a substrate and a medium layer. The aggregates of the developed silver grains are arranged in the medium layer so as to constitute said periodical structure. The element is produced by first selectively exposing a photo-curing resin layer formed on said substrate in which the **silver halide** grains are dispersed so as to selectively photo-cure the photo-curing resin layer, then overall exposing the photo-curing resin layer to expose the **silver halide** grains in the photo-curing resin layer, and thereafter developing the photo-curing resin layer.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2003:265124 USPATFULL
TI Optical functional element and method of producing the same
IN Nagao, Kimitoshi, Kanagawa, JAPAN
PA FUJI PHOTO FILM CO., LTD. (non-U.S. corporation)
PI US 2003186139 A1 20031002
US 6767676 B2 20040727
AI US 2003-396504 A1 20030326 (10)
PRAI JP 2002-85851 20020326
JP 2002-229702 20020807
DT Utility
FS APPLICATION
LREP SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W., WASHINGTON, DC,
20037
CLMN Number of Claims: 15
ECL Exemplary Claim: 1
DRWN 3 Drawing Page(s)
LN.CNT 590

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 13 OF 17 USPATFULL on STN

AB A system for imposing a filter between a vehicle driver's eyes and a source of light including at least one detector facing inward into a compartment in the vehicle toward a likely position of the head of the vehicle driver and arranged to obtain images of the eyes of the driver and a processor coupled to the detector(s) and arranged to determine the location of the driver's eyes based on analysis of the images obtained by the detector(s) and to obtain information about objects exterior of the vehicle providing sources of light from the images obtained by the detector(s) based on reflections off of the driver's eyes, i.e., the position of such objects. A filter, such as a pixelated screen, is imposed between the sources of light and the driver's eyes based on the location of the driver's eyes and the information about the exterior objects providing the sources of light.

AN 2003:242806 USPATFULL
TI Enhanced vision for driving
IN Spero, Yechezkal Evan, Moshav Tifrach, ISRAEL
PI US 2003169213 A1 20030911
AI US 2003-383997 A1 20030307 (10)
PRAI US 2002-362078P 20020307 (60)
US 2002-384845P 20020604 (60)
DT Utility
FS APPLICATION
LREP BRIAN ROFFE, ESQ, 11 SUNRISE PLAZA, SUITE 303, VALLEY STREAM, NY,
11580-6170
CLMN Number of Claims: 20
ECL Exemplary Claim: 1
DRWN 5 Drawing Page(s)
LN.CNT 1543

L8 ANSWER 14 OF 17 USPATFULL on STN
AB Systems including apparatus, methods, compositions, and kits for multiplexed analysis of biological samples or reagents using coded particles. The coded particles may be used to form positionally flexible arrays of samples and/or reagents in which the samples and/or reagents are identified by codes on the particles.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2003:187864 USPATFULL
TI Coded particles for multiplexed analysis of biological samples
IN Ravkin, Ilya, Palo Alto, CA, UNITED STATES
Goldbard, Simon, San Jose, CA, UNITED STATES
Zarowitz, Michael A., San Carlos, CA, UNITED STATES
Hyun, William C., San Francisco, CA, UNITED STATES
PI US 2003129654 A1 20030710
AI US 2002-273605 A1 20021018 (10)
RLI Continuation-in-part of Ser. No. US 2000-549970, filed on 14 Apr 2000,
PENDING Continuation-in-part of Ser. No. US 2000-694077, filed on 19 Oct
2000, PENDING Continuation-in-part of Ser. No. US 2002-120900, filed on
10 Apr 2002, PENDING
PRAI WO 2001-US51413 20011018
US 2001-343682P 20011026 (60)
US 2001-343685P 20011026 (60)
US 2001-344482P 20011026 (60)
US 2002-413675P 20020924 (60)
US 2002-359207P 20020221 (60)
US 2001-345606P 20011026 (60)
US 2001-344483P 20011026 (60)
US 1999-170947P 19991215 (60)
US 1999-129664P 19990415 (60)
US 2001-348025P 20011026 (60)
US 2001-348027P 20011026 (60)
US 2002-362001P 20020305 (60)
US 2002-362055P 20020305 (60)
US 2002-362238P 20020305 (60)
US 2002-370313P 20020404 (60)
US 2002-383091P 20020523 (60)
US 2002-383092P 20020523 (60)
US 2002-413407P 20020924 (60)
DT Utility
FS APPLICATION
LREP KOLISCH HARTWELL, P.C., 520 S.W. YAMHILL STREET, SUITE 200, PORTLAND,
OR, 97204
CLMN Number of Claims: 65
ECL Exemplary Claim: 1
DRWN 22 Drawing Page(s)

LN.CNT 5036

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 15 OF 17 USPATFULL on STN

AB Wafer-level electronic packages having waveguides and methods of fabricating chip-level electronic packages having waveguides are disclosed. A representative chip-level electronic package includes at least one waveguide having a waveguide core. In addition, another representative chip-level electronic package includes a waveguide having an air-gap cladding layer around a portion of the waveguide core. A representative method for fabricating a chip-level electronic package includes: providing a substrate having a passivation layer disposed on the substrate; disposing a waveguide core on a portion of the passivation layer; disposing a first sacrificial layer onto at least one portion of the passivation layer and the waveguide core; disposing an overcoat layer onto the passivation layer and the first sacrificial layer; and removing the first sacrificial layer to define an air-gap cladding layer within the overcoat polymer layer and around a portion of the waveguide core.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:250548 USPATFULL

TI Guided-wave optical interconnections embedded within a microelectronic wafer-level batch package

IN Mule', Tony, Atlanta, GA, UNITED STATES

Patel, Chirag, Jonesboro, GA, UNITED STATES

Meindl, James D., Marietta, GA, UNITED STATES

Gaylord, Thomas K., Atlanta, GA, UNITED STATES

Glytsis, Elias N., Dunwoody, GA, UNITED STATES

Martin, Kevin P., Atlanta, GA, UNITED STATES

Schultz, Stephen M., Spanish Fork, UT, UNITED STATES

Bakir, Muhamnad, Atlanta, GA, UNITED STATES

Reed, Hollie, Smyrna, GA, UNITED STATES

Kohl, Paul, Atlanta, GA, UNITED STATES

PI US 2002136481 A1 20020926

US 6785458 B2 20040831

AI US 2002-74420 A1 20020211 (10)

PRAI US 2001-268142P 20010211 (60)

DT Utility

FS APPLICATION

LREP THOMAS, KAYDEN, HORSTEMEYER & RISLEY, LLP, 100 GALLERIA PARKWAY, NW, STE 1750, ATLANTA, GA, 30339-5948

CLMN Number of Claims: 30

ECL Exemplary Claim: 1

DRWN 34 Drawing Page(s)

LN.CNT 1591

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 16 OF 17 USPAT2 on STN

AB The optical functional element contains aggregates of developed silver grains obtained by developing **silver halide** grains arranged so as to constitute a periodical structure. The element includes a substrate and a medium layer. The aggregates of the developed silver grains are arranged in the medium layer so as to constitute said periodical structure. The element is produced by first selectively exposing a photo-curing resin layer formed on said substrate in which the **silver halide** grains are dispersed so as to selectively photo-cure the photo-curing resin layer, then overall exposing the photo-curing resin layer to expose the **silver halide** grains in the photo-curing resin layer, and thereafter developing the photo-curing resin layer.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2003:265124 USPAT2
TI Optical functional element and method of producing the same
IN Nagao, Kimitoshi, Kanagawa, JAPAN
PA Fuji Photo Film Co., Ltd., Kanagawa, JAPAN (non-U.S. corporation)
PI US 6767676 B2 20040727
AI US 2003-396504 20030326 (10)
PRAI JP 2002-85851 20020326
JP 2002-229702 20020807
DT Utility
FS GRANTED
EXNAM Primary Examiner: McPherson, John A.; Assistant Examiner: Walke, Amanda
LREP Sughrue Mion, PLLC
CLMN Number of Claims: 15
ECL Exemplary Claim: 1
DRWN 10 Drawing Figure(s); 3 Drawing Page(s)
LN.CNT 583
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 17 OF 17 USPAT2 on STN
AB Wafer-level electronic packages having waveguides and methods of fabricating chip-level electronic packages having waveguides are disclosed. A representative chip-level electronic package includes at least one waveguide having a waveguide core. In addition, another representative chip-level electronic package includes a waveguide having an air-gap cladding layer around a portion of the waveguide core. A representative method for fabricating a chip-level electronic package includes: providing a substrate having a passivation layer disposed on the substrate; disposing a waveguide core on a portion of the passivation layer; disposing a first sacrificial layer onto at least one portion of the passivation layer and the waveguide core; disposing an overcoat layer onto the passivation layer and the first sacrificial layer; and removing the first sacrificial layer to define an air-gap cladding layer within the overcoat polymer layer and around a portion of the waveguide core.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:250548 USPAT2
TI Guided-wave optical interconnections embedded within a microelectronic wafer-level batch package
IN Mule', Tony, Atlanta, GA, United States
Patel, Chirag, College Park, GA, United States
Meindl, James D., Marietta, GA, United States
Gaylord, Thomas K., Atlanta, GA, United States
Glytsis, Elias N., Dunwoody, GA, United States
Martin, Kevin P., Atlanta, GA, United States
Schultz, Stephen M., Tucson, AZ, United States
Bakir, Muhamnad, Atlanta, GA, United States
Reed, Hollie, Smyrna, GA, United States
Kohl, Paul, Atlanta, GA, United States
PA Georgia Tech Research Corporation, Atlanta, GA, United States (U.S. corporation)
PI US 6785458 B2 20040831
AI US 2002-74420 20020211 (10)
PRAI US 2001-268142P 20010211 (60)
DT Utility
FS GRANTED
EXNAM Primary Examiner: Glick, Edward J.; Assistant Examiner: Artman, Thomas R
LREP Thomas, Kayden, Horstemeyer & Risley, LLP
CLMN Number of Claims: 13
ECL Exemplary Claim: 12
DRWN 210 Drawing Figure(s); 40 Drawing Page(s)
LN.CNT 1538
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> d his

(FILE 'HOME' ENTERED AT 10:16:25 ON 14 MAR 2005)

FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2' ENTERED AT 10:16:47 ON
14 MAR 2005

L1 13360 S (PHOTONIC) (8A) (CRYSTAL#)
L2 81171 S (SILVER(W) HALIDE)
L3 22170 S (SPECTRAL(4A) SENSITIV?)
L4 7468 S (CHEMICAL(4A) SENSITIZAT?)
L5 1 S L1 AND L2 AND L3 AND L4
L6 28 S L1 AND L2
L7 782039 S (WAVELENGTH#)
L8 17 S L6 AND L7

=>

=> d his

(FILE 'HOME' ENTERED AT 10:16:25 ON 14 MAR 2005)

FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2' ENTERED AT 10:16:47 ON
14 MAR 2005

L1 13360 S (PHOTONIC) (8A) (CRYSTAL#)
L2 81171 S (SILVER(W) HALIDE)
L3 22170 S (SPECTRAL(4A) SENSITIV?)
L4 7468 S (CHEMICAL(4A) SENSITIZAT?)

=> s l1 and l2 and l3 and l4

L5 1 L1 AND L2 AND L3 AND L4

=> d abs,bib

L5 ANSWER 1 OF 1 USPATFULL on STN

AB A photonic crystal manufacturing method exposes two or more silver halide particle layers that contain silver halide particles which have different spectral sensitivity characteristics for each of the silver halide particle layers to light having wavelengths corresponding to the respective different spectral sensitivity characteristics, and then develops the exposed silver halide particle layers to form therein a periodic structure with an aggregate of developed silver. Photonic crystals can be manufactured with relative ease in a relatively short period of time. This method assures continued high accuracy.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2004:73766 USPATFULL

TI Method of manufacturing photonic crystal

IN Miyazaki, Keiichi, Kanagawa, JAPAN

PA FUJI PHOTO FILM CO., LTD. (non-U.S. corporation)

PI US 2004055528 A1 20040325

AI US 2003-667361 A1 20030923 (10)

PRAI JP 2002-276867 20020924

DT Utility

FS APPLICATION

LREP SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W., SUITE 800,
WASHINGTON, DC, 20037

CLMN Number of Claims: 9

ECL Exemplary Claim: 1

DRWN 2 Drawing Page(s)

LN.CNT 359

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=>

Day : Monday
 Date: 3/14/2005

Time: 09:11:30


PALM INTRANET
Inventor Name Search Result

Your Search was:

Last Name = MIYAZAKI

First Name = KEIICHI

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>07278130</u>	Not Issued	161	11/30/1988	PHOTOGRAPHIC PRINTS AND A METHOD FOR THEIR MANUFACTURE	MIYAZAKI, KEIICHI
<u>08668588</u>	5966701	150	06/19/1996	RECOGNITION AND JUDGEMENT APPARATUS HAVING VARIOUS LEARNING FUNCTIONS	MIYAZAKI, KEIICHI
<u>09325546</u>	6636631	150	06/04/1999	OPTICAL CHARACTER READING METHOD AND SYSTEM FOR A DOCUMENT WITH RULED LINES AND ITS APPLICATION	MIYAZAKI, KEIICHI
<u>09478437</u>	6500607	150	01/06/2000	SILVER HALIDE PHOTOGRAPHIC MATERIAL	MIYAZAKI, KEIICHI
<u>09604435</u>	6643407	150	06/28/2000	METHOD OF COMPRESSING MULTI-SPECTRAL IMAGE	MIYAZAKI, KEIICHI
<u>09819203</u>	Not Issued	094	03/28/2001	APPARATUS AND METHOD FOR REPRODUCING PICTURE SIGNAL	MIYAZAKI, KEIICHI
<u>09819955</u>	Not Issued	030	03/28/2001	APPARATUS AND METHOD FOR DECOMPRESSING COMPRESSED DATA	MIYAZAKI, KEIICHI
<u>09820325</u>	6842485	150	03/29/2001	METHOD AND APPARATUS FOR REPRODUCING COMPRESSIVELY CODED DATA	MIYAZAKI, KEIICHI
<u>10254773</u>	6773122	150	09/26/2002	OPTICAL FILM CONTAINING ANTI-GLARE LAYER AND IMAGE DISPLAY APPARATUS USING THE SAME	MIYAZAKI, KEIICHI
<u>10667361</u>	Not Issued	030	09/23/2003	METHOD OF MANUFACTURING	MIYAZAKI, KEIICHI

				PHOTONIC CRYSTAL	
10880471	Not Issued	030	07/01/2004	LIQUID CRYSTAL DISPLAY	MIYAZAKI, KEIICHI
10942144	Not Issued	020	09/16/2004	IMAGING DISPLAY APPARATUS	MIYAZAKI, KEIICHI
07425235	4981269	150	10/23/1989	VERTICAL MILL	MIYAZAKI, KEIICHIRO

Inventor Search Completed: No Records to Display.

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Last Name <input type="text" value="Miyazaki"/>	First Name <input type="text" value="Keiichi"/>	<input type="button" value="Search"/>
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6, 767, 676

114/89, 95*, 97*

10/667, 361

Examiner's Notes

Inventor Name Search Completed

S(photonics) (8a) (crystal #)

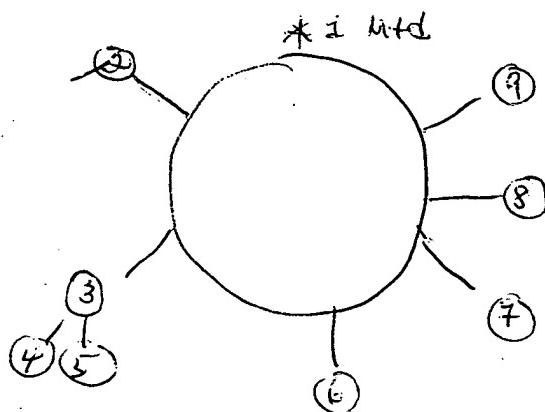
S(silver(w) halide or)

S(spectral (4a) sensitiv?)

S(wavelength#)

S(chemical (4a)sensitization#)

10/117, 479
055, 528



* Motivation - the production of a photonic crystal w/ laser & a short period of time